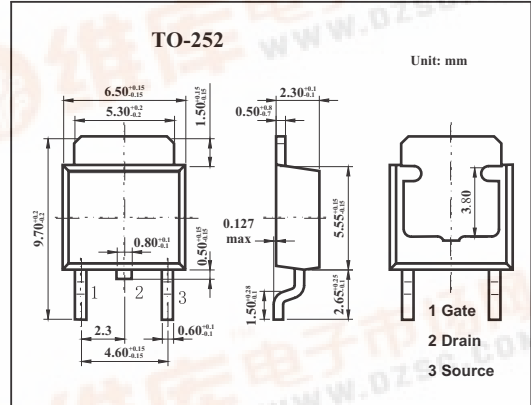
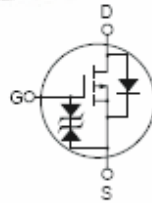


SMD Type MOSFET

High Speed Power Switching
2SJ528S

Features

- Low on-resistance
R_{DS(on)} = 0.17 Ω typ.
- High speed switching
- 4V gate drive devices.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current (DC)	I _D	-7	A
Drain current(pulse) *	I _D	-28	A
Power dissipation	P _D	20	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, duty cycle ≤ 1 %

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain to source breakdown voltage	V _{DSS}	I _D =-10mA, V _{GS} =0	-60			V
Gate to source breakdown voltage	V _{GSS}	I _G =±100 μA, V _{DS} =0	±20			V
Drain cut-off current	I _{DSS}	V _{DS} =-60V, V _{GS} =0			-10	μA
Gate leakage current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Gate to source cutoff voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0		-2.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-10V, I _D =-4A	3.0	5.0		S
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-4A		0.17	0.22	Ω
		V _{GS} =-4.0V, I _D =-4A		0.24	0.37	Ω
Input capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0, f=1MHZ		440		pF
Output capacitance	C _{oss}				220	pF
Reverse transfer capacitance	C _{rss}				75	pF
Turn-on delay time	t _{d(on)}	V _{GS(on)} =-10V, I _D =-4A, R _L =7.5 Ω		10		ns
Rise time	t _r			40		ns
Turn-off delay time	t _{d(off)}				75	ns
Fall time	t _f				65	ns

